Analog Power AM7152N

N-Channel 150-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

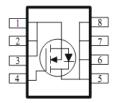
Typical	Applications
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- · PoE PSE and PD Circuits
- LED Inverter Circuits
- 48V-Input DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
150	156 @ V _{GS} = 10V	3.9		
	$176 @ V_{GS} = 5.5V$	3.7		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			150	V		
Gate-Source Voltage	V_{GS}	±20	V			
Continuous Drain Current a	T _A =25°C		3.9			
Continuous Drain Current	T _A =70°C	I _D	3	Α		
Pulsed Drain Current ^b	I_{DM}	15				
Continuous Source Current (Diode Conduction) a	I _S	4.6	Α			
Power Dissipation ^a	T _A =25°C	P_{D}	3.5	W		
rower Dissipation	T _A =70°C	' D	2	V V		
Operating Junction and Storage Temperature Range			-55 to 150	°C		

COMPLIANT HALOGEN FREE

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	35	°C/W		
Maximum Junction-to-Ambient	Steady State	IXOJA	81	C/VV		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	,	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	6			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_{D} = 2 \text{ A}$			156 mΩ		
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 5.5 \text{ V}, I_D = 1.6 \text{ A}$			176	11152	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 2 \text{ A}$		6		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.79		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 75 \text{ V}, V_{GS} = 5.5 \text{ V},$		13			
Gate-Source Charge	Q_{gs}	$I_{DS} = 73 \text{ V}, V_{GS} = 3.3 \text{ V},$ $I_{D} = 2 \text{ A}$		5.7		nC	
Gate-Drain Charge	Q_{gd}	1D = 2 A		4.8			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 75 \text{ V}, R_{L} = 37.5 \Omega,$		10			
Rise Time	t _r	$V_{DS} = 75 \text{ V}, R_L - 37.3 \Omega,$ $I_D = 2 \text{ A},$		8		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		29		ns	
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.12		9			
Input Capacitance	C _{iss}			1158			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		81		pF	
Reverse Transfer Capacitance	C_{rss}			45			

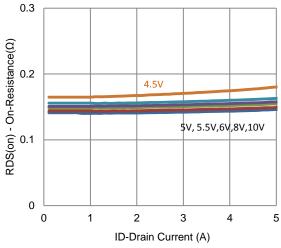
Notes

- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

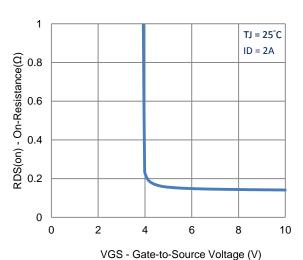
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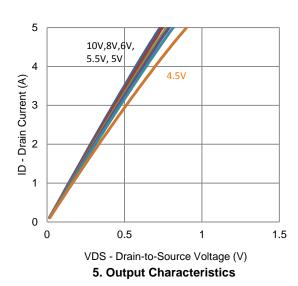
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



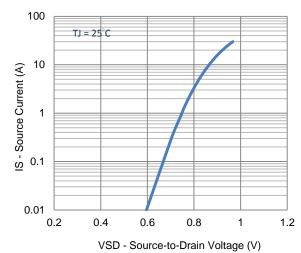
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TJ = 25°C

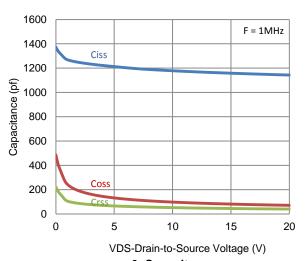
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2. Transfer Characteristics



4. Drain-to-Source Forward Voltage



6. Capacitance

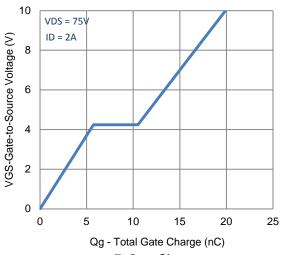
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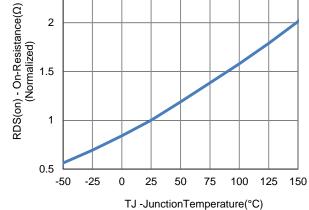
Typical Electrical Characteristics

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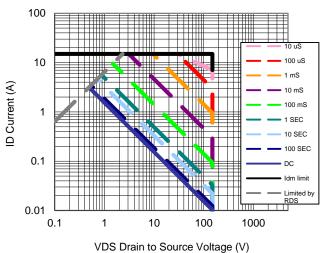
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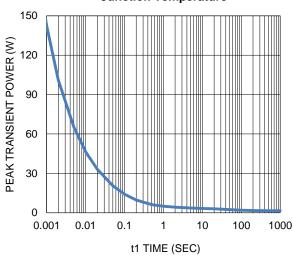




7. Gate Charge

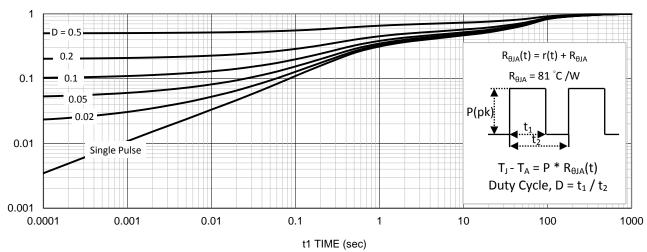






9. Safe Operating Area

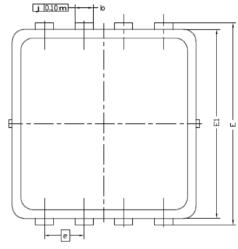
10. Single Pulse Maximum Power Dissipation

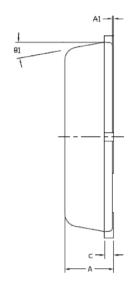


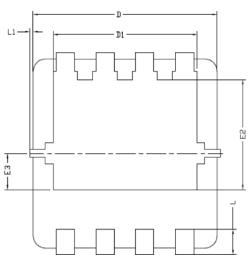
11. Normalized Thermal Transient Junction to Ambient

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Package Information







птм	MILLIMETERS			INCHES			
DIM,	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.700	0,80	0.900	0,0276	0,0315	0,0354	
A1	0.00		0.05	0,000		0.002	
b	0.24	0.30	0.35	0.009	0.012	0.014	
C	0.10	0.152	0.25	0.004	0.006	0.010	
D	3.00 BSC			0.118 BSC			
D1	2.35 BSC 0.093				093 BS)C	
Ε	3.20 BSC			0.126 BSC			
E1	3'00 B2C			0.118 BSC			
E2	1.75 BSC			0.069 BSC			
E3	0,575 BSC			0.023 BSC			
е	0.65 BSC			0,026 BSC			
L	0,30	0,40	0,50	0,0118	0,0157	0,0197	
L1	0		0,100	0		0.004	
91	0°	10°	12°	0*	10°	12°	

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